REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-61 are presently active; Claims 1, 28, 55, and 58 have been presently amended. No new matter has been added.

In the outstanding Office Action, Claims 1-61 were rejected under 35 U.S.C. § 112, first paragraph, for not being enabled. Claim 1 was provisionally rejected under the judicially created doctrine of obviousness-type double patenting over Claim 1 of U.S. Pat. Appl. No. 10/673,507. Claim 1 was also provisionally rejected under the judicially created doctrine of obviousness-type double patenting over Claim 1 of U.S. Pat. Appl. Nos. 10/673,501; 10/673,138; and 10/673,583. Claim 58 was rejected under 35 U.S.C. § 101 for being non-statutory. Claims 1-21, 23, 25-48, 50, and 52-61 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Sonderman et al (U.S. Pat. No. 6,802,045) in view of Chen (U.S. Pat. No. 5,719,796) and in view of Jain et al ("Mathematical Physical Engine"). Claims 22 and 49 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Sonderman et al in view of Chen and Jain further in view of Yunemura et al (IEEE Article, "Heat Analysis on Insulated Metal Substrates"). Claims 24 and 51 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Sonderman et al in view of Chen and Jain further in view of Nikoonahad (U.S. Pat. No. 6,812,045).

Regarding the rejection on the merits:

Briefly recapitulating, Claim 1 defines a method of facilitating a process performed by a semiconductor processing tool including:

> 1) inputting process data relating to an actual process being performed
> by the semiconductor processing tool,
> 2) inputting a first principles physical model including a set of
> computer-encoded differential equations, the first principles physical model

> describing at least one of a basic physical or chemical attribute of the
> semiconductor processing tool,
>
> 3) performing first principles simulation for the actual process being
> performed during performance of the actual process using the physical model
> to provide a first principles simulation result in accordance with the process
> data relating to the actual process being performed in order to simulate the
> actual process being performed, *said first principles simulation result being
> produced in a time frame shorter in time than the actual process being
> performed,*
>
> 4) using the first principles simulation result obtained during
> performance of the actual process to build an empirical model, and
>
> 5) selecting at least one of the first principles simulation result and the
> empirical model to control the actual process being performed by the
> semiconductor processing tool,[1]

The claim defines clearly a process where data input from an actual process being performed

is used for producing a first principles simulation result, produced for the actual process

being performed during performance of the actual process. The result obtained is then used

during performance of the actual process to build an empirical model. The first principles

simulation result and/or the empirical model is available to control the actual process being

performed.

M.P.E.P. § 2164.01 states that the test of enablement is whether one reasonably

skilled in the art could make or use the invention from the disclosures in the patent coupled

with information known in the art *without undue experimentation*. Applicant resubmits that

details of what basic physical and chemical attribute of the semiconductor processing tool are

used to construct the first principle simulation model are disclosed in Applicant's filed

specification at pages 7 and 8 by numbered paragraphs [0035] and [0036] which state that

> First principles physical model 106 is a model of the physical attributes
> of the tool and tool environment as well as the fundamental equations
> necessary to perform first principles simulation and provide a simulation result
> for facilitating a process performed by the semiconductor processing tool.
> Thus, the first principles physical model 106 depends to some extent on the
> type of semiconductor processing tool 102 analyzed as well as the process
> performed in the tool. For example, the physical model 106 may include a

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[1] The enumerations have been added purely for the purpose of referencing these elements in the present
discussion.

spatially resolved model of the physical geometry of the tool 102, which is different, for example, for a chemical vapor deposition (CVD) chamber and a diffusion furnace. Similarly, the first principles equations necessary to compute flow fields are quite different than those necessary to compute temperature fields. The physical model 106 may be a model as implemented in commercially available software, such as ANSYS, of ANSYS Inc., Southpointe, 275 Technology Drive Canonsburg, PA 15317, FLUENT, of Fluent Inc., 10 Cavendish Ct. Centerra Park, Lebanon, NH 03766, or CFD-ACE+, of CFD Research Corp., 215 Wynn Dr., Huntsville, AL 35805, to compute flow fields, electro-magnetic fields, temperature fields, chemistry, surface chemistry (i.e. etch surface chemistry or deposition surface chemistry). However, special purpose or custom models developed from first principles to resolve these and other details within the processing system may also be used.

First principles simulation processor 108 is a processing device that applies data input from the data input device 104 to the first principles physical model 108 to execute a first principles simulation. Specifically, the first principles simulation processor 108 may use the data provided by the data input device 104 to set initial conditions and/or boundary conditions for the first principles physical model 106, which is then executed by the simulation module. First principles simulations in the present invention include, but are not limited to, simulations of electro-magnetic fields derived from Maxwell's equations, continuum simulations, for example, for mass, momentum, and energy transport derived from continuity, the Navier-Stokes equation and the First Law of Thermodynamics, as well as atomistic simulations derived from the Boltzmann equation, such as for example Monte Carlo simulations of rarefied gases (see Bird, G.A. 1994. Molecular gas dynamics and the direct simulation of gas flows, Clarendon Press). First principles simulation processor 108 may be implemented as a processor or workstation physically integrated with the semiconductor processing tool 102, or as a general purpose computer system such as the computer system 1401 of Figure 14. The output of the first principles simulation processor 108 is a simulation result that is used to facilitate a process performed by the semiconductor processing tool 102. For example, the simulation result may be used to facilitate process development, process control and fault detection as well as to provide virtual sensor outputs that facilitate tool processes, as will be further described below.

Furthermore, the subject matters of Claims 6, 8 and 9 (and the supporting details in the specification) provide details of inputting data and computer codes for performing the first principles simulation result.

Thus, one of ordinary skill in the art, knowing from the specification that these codes are commercially available software programs, would **not** have to use undue experimentation to apply the respective physical attributes that each model is tailored to in order to perform the claimed inputting a first principles physical model step.

The outstanding Office Action requests details of the models which lead to the unexpected result of being able to avoid the lengthy time for the generation of a first principles model simulation. Applicant points out the subject matter of Claims 15-19 and 59-61 as providing procedures by which the unexpected results of the present invention are achieved. These disclosed characteristics permit simulation results to be obtained in a time frame compatible with using the first principles model simulation result for real time process control:

1) the use of interconnected resources inside a semiconductor device manufacturing facility to perform the first principles simulation,

2) the use of code parallelization among interconnected computational resources inside the semiconductor device manufacturing facility,

3) the sharing of simulation information among interconnected resources inside the semiconductor device manufacturing facility, and

4) the reduction in redundant execution of substantially similar first principles simulations by different resources the reuse of known solutions as initial conditions for the first principles simulation, as features which used singularly or in combination lead to a simulation result in a time frame consistent with real time process control in a semiconductor processing tool.

Below are Claims 15-19 and 59 reproduced for the examiner's convenience showing the networking of interconnected resources inside a semiconductor device manufacturing facility, the sharing of computational load, and the distribution of similar simulation results (for example as initial boundary conditions) to reduce redundant refinements and execution and permit a first principles simulation result to be produced in a time frame shorter in time than the actual process being performed:

Claim 15. The method of Claim 1, further comprising using a network of interconnected resources inside a semiconductor device manufacturing facility to perform the first principles simulation recited in Claim 1.

Claim 16. The method of Claim 15, further comprising using code parallelization among interconnected computational resources to share the computational load of the first principles simulation.

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Claim 17. The method of Claim 15, further comprising sharing simulation information among interconnected resources to facilitate a process performed by the semiconductor processing tool.

Claim 18. The method of Claim 17, wherein said sharing simulation information comprises distributing simulation results among the interconnected resources to reduce redundant execution of substantially similar first principles simulations by different resources.

Claim 19. The method of Claim 17, wherein said sharing simulation information comprises distributing model changes among the interconnected resources to reduce redundant refinements of first principles simulations by different resources.

Claim 59. The method of Claim 1, wherein said performing a first principles simulation comprises:
providing for the first principles simulation a reuse of known solutions as initial conditions for the first principles simulation.

Hence, it is respectfully submitted that, in view of the disclosure of commercial software available for the different physical models disclosed and in view of the disclosure of procedures by which the time for producing a first principles model simulation result can be reduced, the 35 U.S.C. § 112, first paragraph, rejection should be withdrawn.

Regarding the rejection on the merits:

The Office Action makes clear on pages 5 and 6 that the Examiner and the Applicant disagree as to whether the subscripts in <u>Sonderman et al</u> S_i associated with the silicon wafer disclosure refers to process control for the same wafer being processed or process control for subsequent wafers. The Examiner's position is that <u>Sonderman et al</u> would have used S_{i+1} to designate subsequent wafers.

Yet, Applicant respectfully points out that, at col. 9, lines 46-51, <u>Sonderman et al</u> specifically states:

The system 100 *then* optimizes the simulation (described above) to find more optimal process target (T_i) for each silicon wafer, *S_i to be processed*. These target values are then used *to* generate *new control inputs, X_{Ti},* on the line 805 to control *a subsequent process of a silicon wafer S_i*. [Emphasis added]

The plain reading of this section of <u>Sonderman et al</u> is that the system 100 *then* (e.g., at time

T1) optimizes the simulation for each silicon wafer, S_i *to be processed* (e.g., later at time T2).

In other words, the simulation results of <u>Sonderman et al</u> produce a new control input for

each silicon wafer *to be processed*. Thus, Applicant respectfully submits that <u>Sonderman et</u>

<u>al</u> teach performing first principles simulation for the actual process to be performed *before*

performance of the actual process, and **not** the claimed performing first principles simulation

for the actual process being performed during performance of the actual process.

Other sections of <u>Sonderman et al</u> support Applicant's position on this matter.

In the last filed response, Figure 4 of <u>Sonderman et al</u> was pointed out for clearly

showing that the simulation results are produced *ahead of performing a process* and thus

have to be based on historical data, and not based on the actual process being performed
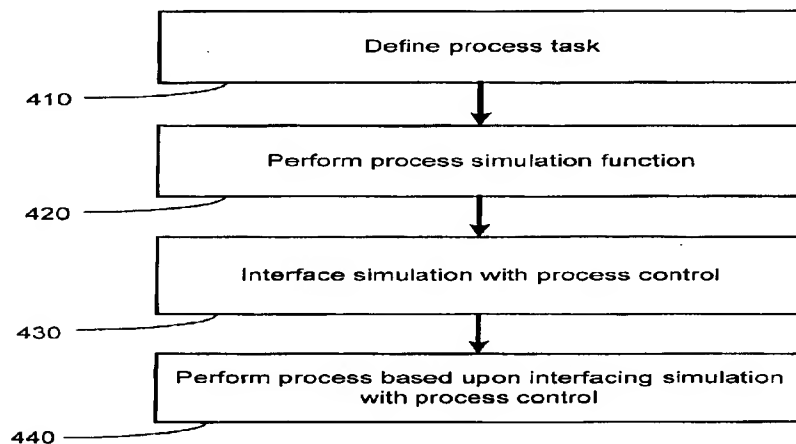
during performance of the actual process.

FIGURE 4

With reference to Figure 4, <u>Sonderman et al</u> disclose at col. 6, lines 24-47:

> Turning now to FIG. 4, a flow chart representation of the methods in accordance with the present invention is illustrated. In one embodiment, *the system 100 defines a process task that is to be performed (block 410)*. The

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process task maybe a photolithography process, an etching process, and the like. *The system 100 then performs a process simulation function* (block 420). A more detailed description of the process simulation function described in block 420, is illustrated below. In one embodiment, a simulation data set results from the execution of the process simulation function.

> *Once the system 100 performs the process simulation function, the system 100 performs an interfacing function*, which facilitates interfacing of the simulation data with the process control environment 180 (block 430). The process control environment 180 can utilize the simulation data in order to modify or define manufacturing control parameters that control the actual processing steps performed by the system 100. *Once the system 100 interfaces the simulation data with the process control environment 180, the system 100 then performs a manufacturing process* based upon the manufacturing parameters defined by the process control environment 180 (block 440). [Emphasis added]

Hence, the process flow in <u>Sonderman et al</u> is straightforward:

1) define process to be modeled,

2) model process for simulation result,

3) interface simulation result to processor, and then

4) run the process under control based on the pre-existing simulation result.

In the outstanding Office Action, the examiner disagreed with this "interpretation" of <u>Sonderman et al</u> and asserted that "the interpretation is incomplete with the reference that this process involves a feedback." The examiner points out part of <u>Sonderman et al</u>'s disclosure with emphasis added by underscoring. This characterization is repeated below for the sake of convenience with the examiner's emphasis.

> Furthermore, the simulation environment 210 can be used for feedback modification of control parameters invoked by the process control environment 180. <u>For example, the manufacturing environment 170 can send metrology data results into the simulation environment 210. The simulation environment 210 can then use the metrology data results and perform various tests and calculations to provide more accurate, modified control parameters to the process control environment 180.</u> A feedback loop in then completed when the process control environment 180 sends the modified or adjusted process control parameters to the manufacturing environment 170 for further processing of semiconductor wafers. {Examiner's emphasis added.}

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Yet, Applicant respectfully points out that this description in <u>Sonderman et al</u> is a description of feedback modification of control parameters. Feedback modification is by definition the control of future wafers based on what has already occurred to a previous wafer. Hence, this section supports rather than refutes Applicant's position on this matter.

Accordingly, Applicant respectfully submits that <u>Sonderman et al</u> do not disclose and indeed *teach away* from the present invention where data input from an actual process being performed is used for producing a first principles simulation result, which is produced for the actual process being performed during performance of the actual process.

Lastly, with regard to <u>Sonderman et al</u>, <u>Sonderman et al</u> do not disclose that a simulation result is produced in a time frame shorter in time than the actual process being performed, as presently defined in the independent claims.

The deficiencies in <u>Sonderman et al</u> are not overcome by <u>Chen</u> or <u>Jain et al</u>.

Regarding <u>Chen</u>, the Office Action in rejecting the present claims supplements the teachings of <u>Sonderman et al</u> with the teachings of <u>Chen</u>. In particular, the Office Action relies on <u>Chen</u> for an asserted teaching of building an empirical model. Yet, Applicant points out that <u>Chen</u> supports Applicant's position on the art not disclosing a simulation result produced in a time frame shorter in time than the actual process being performed. <u>Chen</u>'s Field of Invention states that "the present invention relates to a feedback system for analyzing and monitoring a manufacturing process." Later, in the background, <u>Chen</u> states that:

> What is sought is a technique for tracking and analyzing manufacturing processes such that inaccuracies arising from statistical fluctuations, complicated interactions, and measurement errors are avoided or compensated so that process modifications that produce even small differences can be measured, monitored and analyzed.

Thus, the system of <u>Chen</u> relates to tracking and analyzing manufacturing processes for feedback control, which would (if used for process control in any fashion) be used for subsequent wafer processing.

Regarding Jain et al, the Office Action in rejecting the present claims supplements the

teachings of Sonderman et al with the teachings of Jain et al. Jain et al disclose at pages 372-

373 that:

> We *propose* a wafer scale implementation of the MPE. The starting
> point would be a dedicated processing cell, optimized specifically for the PDE
> arithmetic and data routing. Because of the relative simplicity of the cell, it is
> expected that extremely large arrays (8x8 to 32x32) *could be* successfully
> processed on a single piece of silicon using Wafer Scale Integration
> techniques. In fact, we have already laid the foundation for the development
> of such a processing cell. Our Universal Multiply-Subtract-Add [11] *could be*
> adapted for this first cell design. Similarly, our nonlinear coprocessor cell
> [12]-[14] *might be used* in conjunction with the UMSA to provide advanced
> mathematical functions. As suggested in Fig. 2, there would be *courtyards of*
> *processors*, each with two interconnection networks and two memory banks.
> 2-D, 3-D, and 4-D problems could then be mapped for parallel computations.
> Since inter-processor delays are very small (say a few ns), extremely high
> speeds could be achieved. This, together with the high degree of parallelism,
> would result also in high throughout. We *envision* 100 to 1000 processors (on
> one wafer) forming a wafer scale MPE. At a clock frequency of 50 MHz, a
> single wafer could achieve up to 20 GFLOPs performance. With our
> nonlinear coprocessor added, each instruction could equate to multiple floating
> point operations.
>   Furthermore, because of the extendible architecture, several wafers
> *could be* interconnected as shown in Fig. 5 to construct a "stacked" MPE
> wafer system (SMPE). Note that no vertical interconnects within the stack of
> wafers are expected. Tens to hundreds of GFLOPs performance in a volume
> the size of a desk-top computer [15] *could* thus be achieved. However, *these*
> *predictions* ignore the likely technical advances in the next five years; a
> tenfold further increase in performance *might be achievable*. [Emphasis
> Added]

Thus, as emphasized above, the proposed development work in Jain requires the

development of *futuristic* computational equipment which one of ordinary skill in the art

would be reluctant to implement or utilize for the rigorous standards needed in semiconductor

manufacturing.

In the outstanding Office Action, the Examiner indicates that he finds no connection

or legal basis for considering the teachings of Kee et al. Recently published guidelines for

the Patent and Trademark Office, published in Federal Register Vol. 72, No. 195, on

Wednesday October 10, 2007entitled: "Examination Guidelines for Determining

Obviousness under 35 U.S.C. 103 in View of the Supreme Court Decision in KSR

International v. Teleflex Inc," indicate that:

> Office personnel should consider all rebuttal evidence that is timely presented by the applicants when reevaluating any obviousness determination. Rebuttal evidence may include evidence of "secondary considerations," such as "commercial success, long felt but unsolved needs, [and] failure of others", and may also include evidence of unexpected results. Office personnel must articulate findings of fact that support the rationale relied upon in an obviousness rejection. As a result, applicants are likely to submit evidence to rebut the fact finding made by Office personnel. For example, in the case of a claim to a combination, applicants may submit evidence or argument to demonstrate that:
> (1) one of ordinary skill in the art could not have combined the claimed elements by known methods (e.g., due to technological difficulties);
> (2) the elements in combination do not merely perform the function that each element performs separately; or
> (3) the results of the claimed combination were unexpected.
>
> Once the applicant has presented rebuttal evidence, Office personnel should reconsider any initial obviousness determination in view of the entire record. All the rejections of record and proposed rejections and their bases should be reviewed to confirm the continued viability. The Office action should clearly communicate the Office's findings and conclusions, articulating how the conclusions are supported by the findings.

Kee et al, of record, is presented as **_rebuttal evidence_** supporting Applicant's general position that the lengthy time for generation of a first principles model simulation in the prior art prevents one from realizing a real time process control based on a first principles simulation during the actual process. This is evidence of the technological difficulties involved in producing a first principles model simulation result, and under the published guidelines has to be considered.

Kee et al deal with the process control of a Rapid Thermal Processing (RTP) tool and do **not** use real time modeling. RTP tools are tools used in semiconductor manufacturing. Thus, the Kee et al approach represents what one of ordinary skill in the art would have known and expected at the time of the invention. M.P.E.P. § 2141.03 indicates that the examiner must ascertain what would have been obvious to one of ordinary skill in the art at the time of the invention. Further, M.P.E.P. § 2141.03 states that "the importance of

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resolving the level of ordinary skill in the art lies in the necessity of maintaining objectivity in

the obviousness inquiry."

Hence, for these reasons, <u>Kee et al</u> is presented as rebuttal evidence for the examiner's

reconsideration of the patentability of the claims.

<u>Kee et al</u> in detail disclose that:

> The modeling apparatus 101 of the instant invention may also be used to perform an inverse analysis to establish the boundary conditions or parameter values required to achieve a certain function of the thermal system. This allows the apparatus to be used to establish the appropriate process parameters and boundary conditions for the thermal system modeled. In accordance with the instant invention, the inverse analysis can be directly carried out by the modeling apparatus *rather than using the conventional approach, which merely solves the direct problem repeatedly, in a lengthy and costly iterative process*, to determine appropriate input parameters to achieve a desired result. In other words, in accordance with the instant invention, *once a particular thermal process is modeled for a particular set of control parameters*, the device may then be used to automatically obtain the necessary control parameters to achieve a desired result by providing the modeling apparatus with parameters corresponding to the desired result.

> To carry out the inverse analysis, the modeling apparatus 101 includes an inverse parameter input section 104 also connected to input device 103. A user inputs into the modeling apparatus 101 parameters corresponding to desired results, e.g., desired temperature characteristics of the system, which are stored in memory 108. The processing unit 110, under control of modeling program 111, *uses the previously generated model* of the thermal system and the parameters held in memory 108 and derives or predicts particular control parameters to meet the constraints entered through the inverse parameter input section 104. This process is more fully described below in connection with the examples provided.[2] [emphasis added]

Hence, <u>Kee et al</u> explicitly disclose that the *predicted* model of the thermal system is used to

design and control the thermal system. <u>Kee et al</u> exemplify the difficulties of a "conventional

approach" which merely solves the spectral radiation transport equations through "a lengthy

and costly process." These problems forced <u>Kee et al</u> to use *pre-generated model results* for

a control process of a RTP process.

M.P.E.P. § 2143.01(II) states that

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[2] Kee et al, col. 4, lines 21-50.

> The test for obviousness is what the ***combined teachings of the references***
> would have suggested to one of ordinary skill in the art, and ***all teachings in***
> ***the prior art must be considered*** to the extent that they are in analogous arts.
> When the teachings of two or more prior art references conflict, the Examiner
> ***must weigh the power of each reference to suggest solutions*** to one of
> ordinary skill in the art, considering the degree to which one reference ***might***
> ***accurately discredit another***. [Emphasis added.]

The examiner is respectfully requested to reconsider the degree to which Jain et al, Chen, and

Kee et al discredit any suggestion that the examiner may have read from the disclosure of

Sonderman et al.

The Supreme Court in *KSR International Co. v. Teleflex Inc. et al. 2007 U.S. LEXIS*

4745 reinforced the role of *Graham* factors and "teaching away" in deciding obviousness.

The Court stated that:

> In *United States v. Adams*, 383 U. S. 39, 40 (1966), a companion case
> to *Graham*, the Court considered the obviousness of a wet battery that varied
> from prior designs in two ways: It contained water, rather than the acids
> conventionally employed in storage batteries; and its electrodes were
> magnesium and cuprous chloride, rather than zinc and silver chloride. The
> Court recognized that when a patent claims a structure already known in the
> prior art that is altered by the mere substitution of one element for another
> known in the field, the combination must do more than yield a predictable
> result. 383 U. S., at 50-51. It nevertheless rejected the Government's claim
> that Adams's battery was obvious. The Court relied upon the corollary ·
> principle that when the prior art ***teaches away*** from combining certain known
> elements, discovery of a successful means of combining them is more likely to
> be nonobvious. *Id.*, at 51-52. When Adams designed his battery, the prior art
> warned that risks were involved in using the types of electrodes he employed.
> The fact that the elements worked together in ***an unexpected and fruitful***
> ***manner*** supported the conclusion that Adams's design was ***not obvious*** to
> those skilled in the art. [Emphasis added.]

In the present situation, the claimed method of performing a first principles simulation

for the actual process being performed during performance of the actual process produces

more than an expected result in that Sonderman et al (in having to develop *new control*

inputs for each subsequent wafer) can not compensate for real time excursions from the

existing model occurring while the wafer is being processed. In other words, the lengthy

time for generation of a first principles model simulation in the prior art prevents one from

realizing a real time process control based on a first principles simulation during the actual

process. Hence, the claimed processes and systems produce *an unexpected result* in that the

first principles simulation result is produced in a time frame shorter in time than the actual

process being performed, as presently claimed.

For all these reasons, Applicant submits that the present invention patentably defines

over <u>Sonderman et al</u>, <u>Chen</u>, and <u>Jain et al</u>.

Regarding the provisional double-patenting rejection:

Applicants submit that a terminal disclaimer can be filed, if the claims in the present

application and the claims in the co-pending Application Nos. 0/673,507; 10/673,501;

10/673,138; and 10/673,583 remain obvious in view of each other at the time of allowance of

either of these applications. Indeed, M.P.E.P. § 804.02 IV states that, prior to issuance, it is

necessary to disclaim each one of the double patenting references applied. Hence, Applicants

respectfully request that the examiner contact the undersigned should the present arguments

be accepted and should the case be otherwise in a condition for allowance. At that time, a

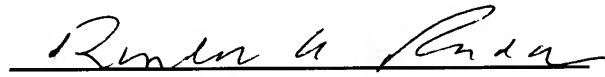terminal disclaimer can be supplied to expedite issuance of this case.

Conclusion:

As argued above, the outstanding rejections for this patent application should be removed, placing all the claims in a condition for allowance.

Consequently, in view of the present amendment and in light of the above discussions, the outstanding grounds for rejection are believed to have been overcome. The application as amended herewith is believed to be in condition for formal allowance. An early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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